

IN THE SPECIFICATION:

The following paragraph replaces paragraph 0038 on page 15 of the specification.

Bandgap voltage reference 516, amplifier 500, PMOS 506, and current sink 514 form a feedback network that may keep NMOS transistor 512 biased such that its gate-source voltage is equal to the NMOS threshold voltage, V_{tn} , over variations in fabrication process parameters and temperature. Since amplifier 500 forces the source of NMOS transistor 512 to be at the same potential as the bandgap voltage reference, the voltage at node 502 may be the sum of the constant bandgap voltage added to the variable NMOS threshold voltage V_{tn} . This voltage is applied to the connected gate and source drain of NMOS transistor 504 whose source is grounded. The V_{tn} portion of the node 502 voltage may bias transistor 504 to the threshold level over variations in process parameters and temperature, but may not produce significant channel current. The V_{bg} portion of the signal may produce a drain-source current in transistor 504 proportional to its beta according to the relationship I_{ds} equals $(\beta/2)(V_{gs}-V_{tn})^2$, since NMOS 504 operates in saturation mode.